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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSVII)

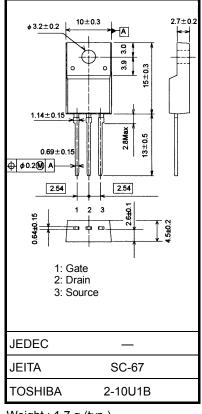
# TK6A60D

#### Switching Regulator Applications

- Low drain-source ON-resistance:  $RDS(ON) = 1.0 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 3.0 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 600 \ V)$
- Enhancement mode:  $V_{th} = 2.0$  to 4.0 V ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1 \text{ mA}$ )

<b>320</b> (1.2 <b>20</b> )								
Characteristics			Symbol	Rating	Unit			
Drain-source voltage			V <sub>DSS</sub>	600	V			
Gate-source voltage			V <sub>GSS</sub>	±30	V			
Drain current	DC (I	Note 1)	۱ <sub>D</sub>	6	А			
	Pulse (I	Note 1)	I <sub>DP</sub>	24	~			
Drain power dissipation (Tc = $25^{\circ}$ C)			PD	40	W			
Single pulse avalanche energy (Note 2)			E <sub>AS</sub>	173	mJ			
Avalanche current			I <sub>AR</sub>	6	А			
Repetitive avalanche energy (Note 3)			E <sub>AR</sub>	4.0	mJ			
Channel temperature			T <sub>ch</sub>	150	°C			
Storage temperature range			T <sub>stg</sub>	-55 to 150	°C			

## Absolute Maximum Ratings (Ta = 25°C)



Weight : 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

#### **Thermal Characteristics**

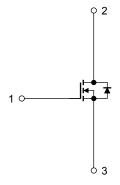
Characteristics	Symbol	Max	Unit	
Thermal resistance, channel to case	R <sub>th (ch-c)</sub>	3.125	°C/W	
Thermal resistance, channel to ambient	R <sub>th (ch-a)</sub>	62.5	°C/W	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial), L = 8.4 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 6 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device. Handle with care.



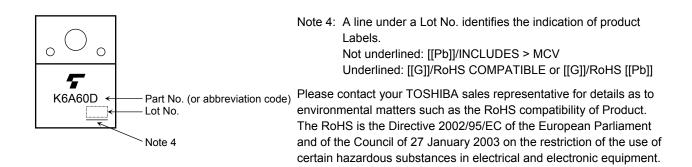
**Electrical Characteristics (Ta = 25°C)** 

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V},  V_{DS} = 0 \text{ V}$	_		±1	μA
Drain cut-off current		I <sub>DSS</sub>	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			10	μA
Drain-source bre	akdown voltage	V (BR) DSS	$_{\rm DSS}$ I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V 600				V
Gate threshold v	oltage	V <sub>th</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.0		4.0	V
Drain-source ON	-resistance	R <sub>DS (ON)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$	_	1.0	1.25	Ω
Forward transfer admittance		Y <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$	0.8	3.0	_	S
Input capacitance		C <sub>iss</sub>		_	800	_	
Reverse transfer capacitance		C <sub>rss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	4	_	pF
Output capacitance		C <sub>oss</sub>	1		100	_	
Switching time	Rise time	tr	$V_{GS}$ $0 V$ $V_{GS}$ $0 V$		20		- ns
	Turn-on time	t <sub>on</sub>			40		
	Fall time	t <sub>f</sub>		_	12	_	
	Turn-off time	t <sub>off</sub>	Duty $\leq$ 1%, t <sub>w</sub> = 10 µs	_	60	—	
Total gate charge		Qg		_	16	—	
Gate-source charge		Q <sub>gs</sub>	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 6\text{A}$	_	10	—	nC
Gate-drain charge		Q <sub>gd</sub>	1	_	6	—	

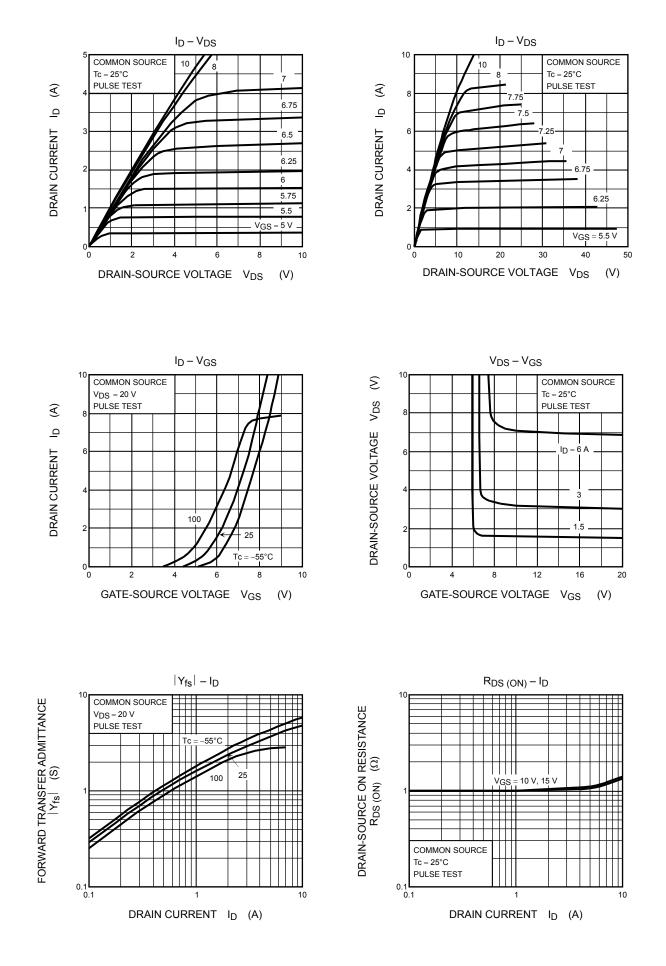
#### Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I <sub>DR</sub>	—	_	_	6	А
Pulse drain reverse current (Note 1)	I <sub>DRP</sub>	—	_	_	24	А
Forward voltage (diode)	V <sub>DSF</sub>	$I_{DR} = 6 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR} = 6 \text{ A}, V_{GS} = 0 \text{ V},$	_	1200	_	ns
Reverse recovery charge	Qrr	dl <sub>DR</sub> /dt = 100 A/μs	_	10	_	μC

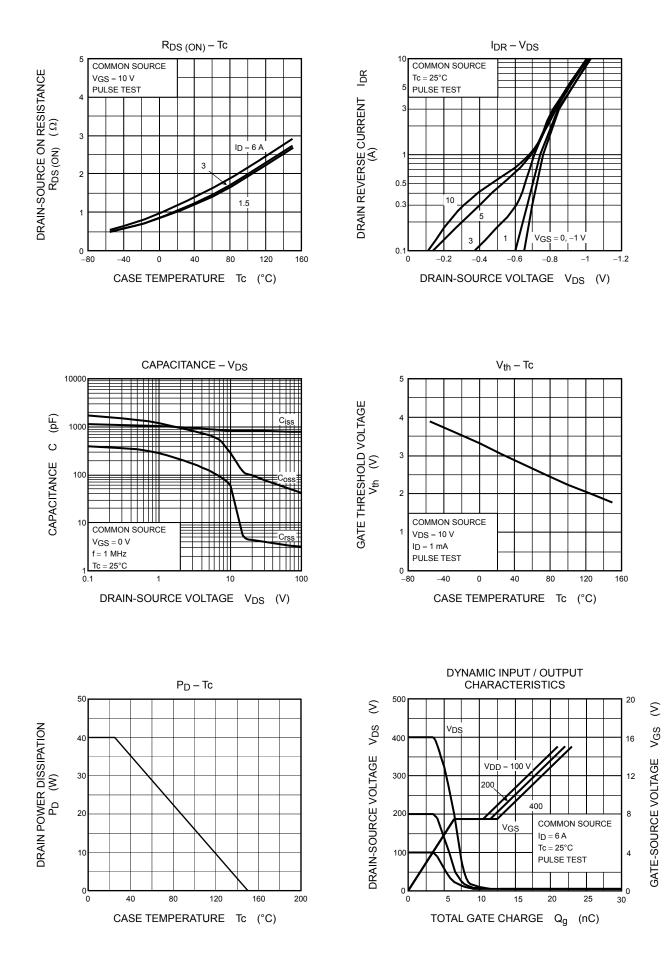
## Marking

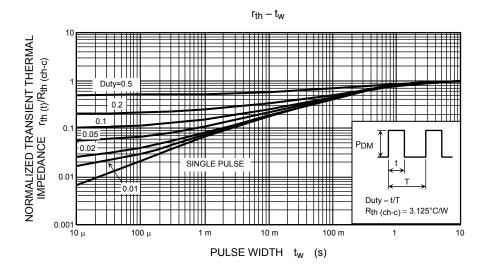


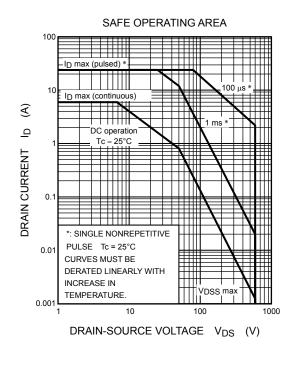
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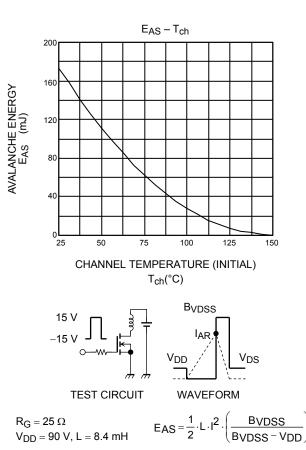


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